

isc Silicon NPN Power Transistor

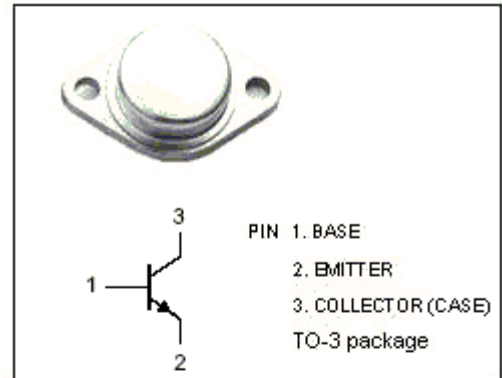
2SD819

DESCRIPTION

- High Collector-Base Breakdown Voltage-  
:  $V_{(BR)CBO} = 1500V$  (Min.)
- Low Collector Saturation Voltage-
- High Switching Speed

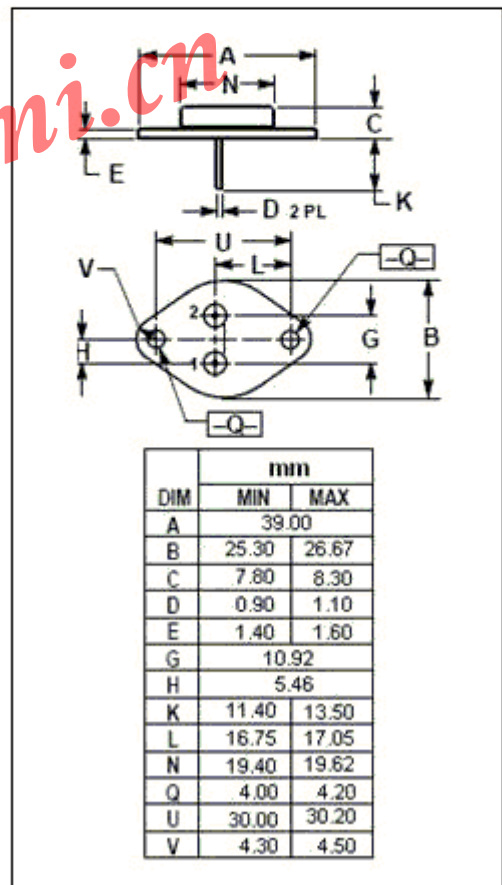
APPLICATIONS

- Designed for color TV horizontal output applications.



ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	MAX	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	600	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	3.5	A
$I_E$	Emitter Current-Continuous	-3.5	A
$P_C$	Collector Power Dissipation @ $T_C=25^{\circ}C$	50	W
$T_j$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-65~150	$^{\circ}C$



## isc Silicon NPN Power Transistor

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## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.8\text{A}$			8.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.8\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=500\text{V}; I_E=0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1.0	mA
$h_{FE}$	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	8			
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{\text{test}}=1.0\text{MHz}$		95		pF
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.1\text{A}; V_{CE}=10\text{V}$		3		MHz
$t_f$	Fall Time	$I_{CP}=3\text{A}; I_{B1(\text{end})}=0.8\text{A}$			1.0	$\mu\text{s}$